



SamHop Microelectronics Corp.

# STM4637

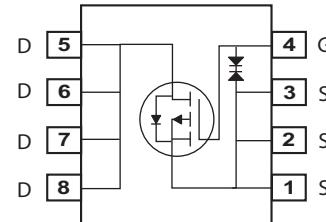
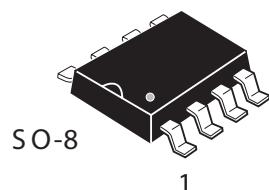
Ver 1.1

## P-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V <sub>DSS</sub>	I <sub>D</sub>	R <sub>DSON</sub> (mΩ) Max
-30V	-7.7A	30 @ V <sub>GSS</sub> =-10V
		48 @ V <sub>GSS</sub> =-4.5V

### FEATURES

- Super high dense cell design for low R<sub>DSON</sub>.
- Rugged and reliable.
- Surface Mount Package.
- ESD Protected.



### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)

Symbol	Parameter	Limit	Units
V <sub>DS</sub>	Drain-Source Voltage	-30	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current-Continuous <sup>a</sup>	-7.7	A
I <sub>DM</sub>	-Pulsed <sup>b</sup>	-35	A
E <sub>AS</sub>	Single Pulse Avalanche Energy <sup>d</sup>	37	mJ
P <sub>D</sub>	Maximum Power Dissipation <sup>a</sup>	2.5	W
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 to 150	°C

### THERMAL CHARACTERISTICS

R <sub>θ JA</sub>	Thermal Resistance, Junction-to-Ambient <sup>a</sup>	50	°C/W
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Details are subject to change without notice.

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## ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>OFF CHARACTERISTICS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =-250uA	-30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-24V , V <sub>GS</sub> =0V			-1	uA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V , V <sub>DS</sub> =0V			±10	uA
<b>ON CHARACTERISTICS</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-1	-1.8	-3	V
R <sub>DSON</sub>	Drain-Source On-State Resistance	V <sub>GS</sub> =-10V , I <sub>D</sub> =-7.7A		24	30	m ohm
		V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-6.2A		36	48	m ohm
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =-15V , I <sub>D</sub> =-7.7A		12.5		S
<b>DYNAMIC CHARACTERISTICS</b> <sup>c</sup>						
C <sub>ISS</sub>	Input Capacitance	V <sub>DS</sub> =-15V,V <sub>GS</sub> =0V f=1.0MHz		1120		pF
C <sub>OSS</sub>	Output Capacitance			280		pF
C <sub>RSS</sub>	Reverse Transfer Capacitance			175		pF
<b>SWITCHING CHARACTERISTICS</b> <sup>c</sup>						
t <sub>D(ON)</sub>	Turn-On Delay Time	V <sub>DD</sub> =-15V I <sub>D</sub> =-1A V <sub>GS</sub> =-10V R <sub>GEN</sub> =6 ohm		15		ns
t <sub>r</sub>	Rise Time			28		ns
t <sub>D(OFF)</sub>	Turn-Off Delay Time			98		ns
t <sub>f</sub>	Fall Time			28		ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =-15V,I <sub>D</sub> =-7.7A,V <sub>GS</sub> =-10V		22		nC
		V <sub>DS</sub> =-15V,I <sub>D</sub> =-6.2A,V <sub>GS</sub> =-4.5V		10.5		nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =-15V,I <sub>D</sub> =-7.7A, V <sub>GS</sub> =-10V		2.5		nC
Q <sub>gd</sub>	Gate-Drain Charge			6.5		nC
<b>DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS</b>						
I <sub>s</sub>	Maximum Continuous Drain-Source Diode Forward Current				-1.7	A
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V,I <sub>s</sub> =-1.7A		-0.9	-1.2	V
<b>Notes</b>						
a.Surface Mounted on FR4 Board,t ≤ 10sec.						
b.Pulse Test:Pulse Width ≤ 300us, Duty Cycle ≤ 2%.						
c.Guaranteed by design, not subject to production testing.						
d.Starting T <sub>J</sub> =25°C,L=1.25mH,R <sub>G</sub> =25Ω,I <sub>AS</sub> =7.7A,V <sub>DD</sub> = 20V,V <sub>GS</sub> =10V.(See Figure13)						

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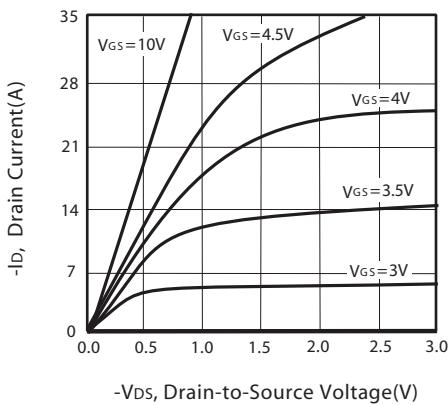


Figure 1. Output Characteristics

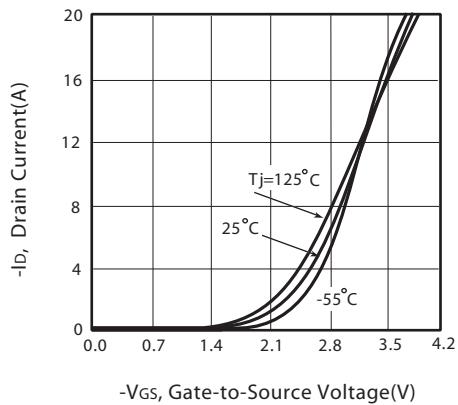


Figure 2. Transfer Characteristics

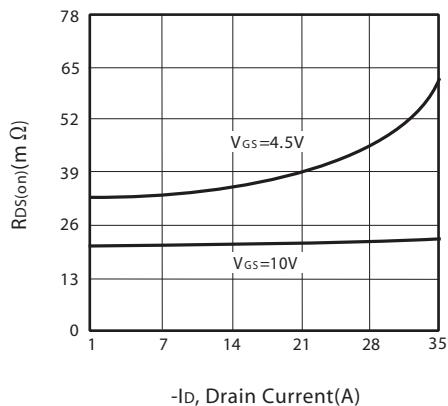


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

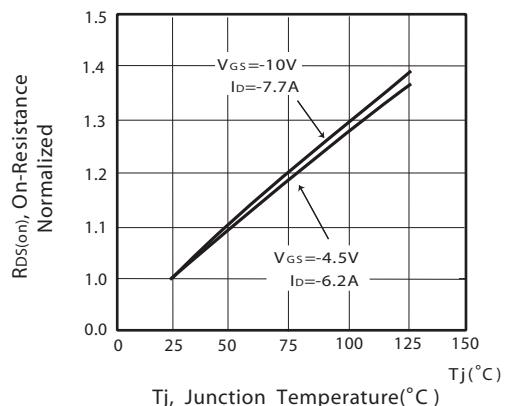


Figure 4. On-Resistance Variation with Drain Current and Temperature

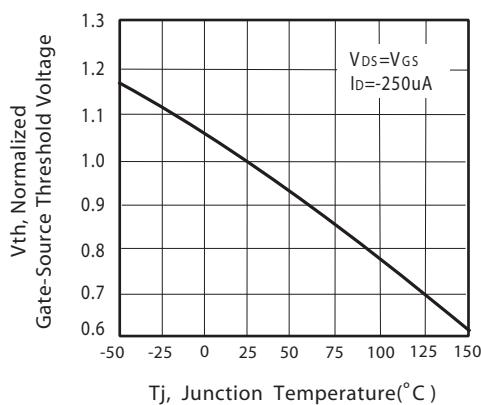


Figure 5. Gate Threshold Variation with Temperature

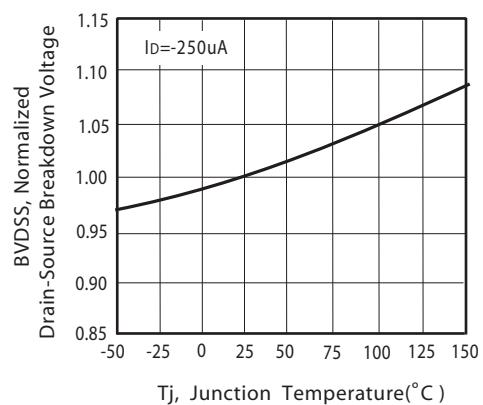


Figure 6. Breakdown Voltage Variation with Temperature

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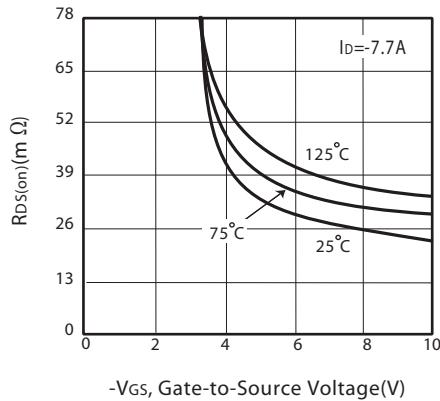


Figure 7. On-Resistance vs.  
Gate-Source Voltage

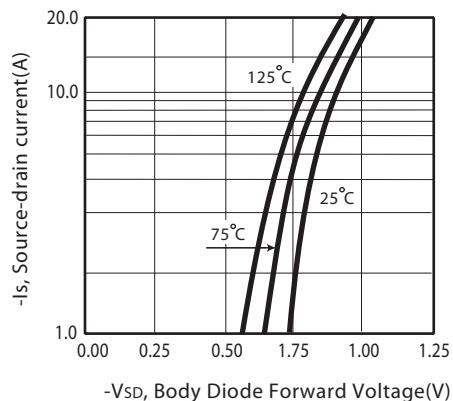


Figure 8. Body Diode Forward Voltage  
Variation with Source Current

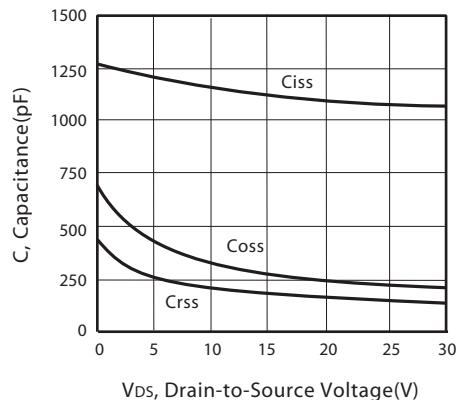


Figure 9. Capacitance

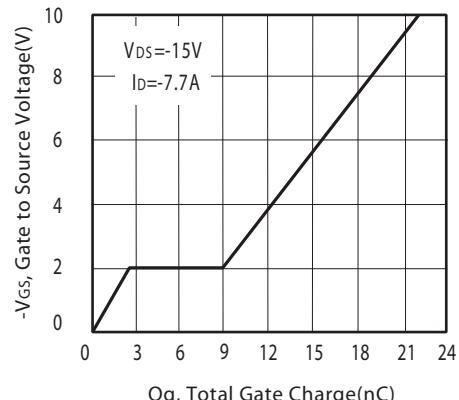


Figure 10. Gate Charge

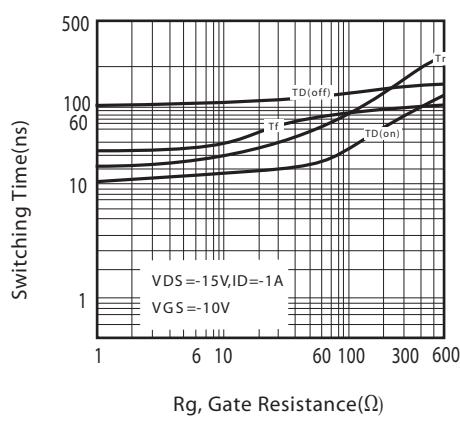


Figure 11. switching characteristics

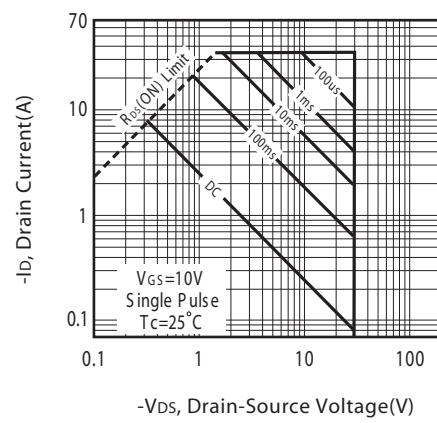
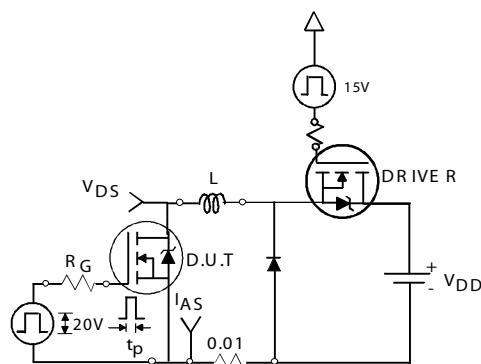


Figure 12. Maximum Safe Operating Area

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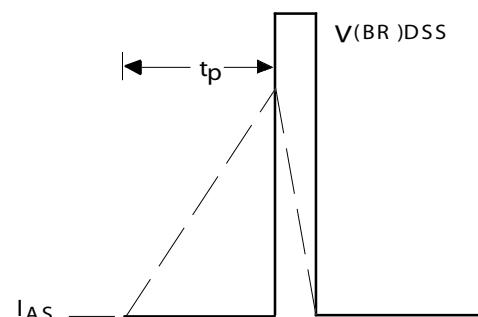
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Unclamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

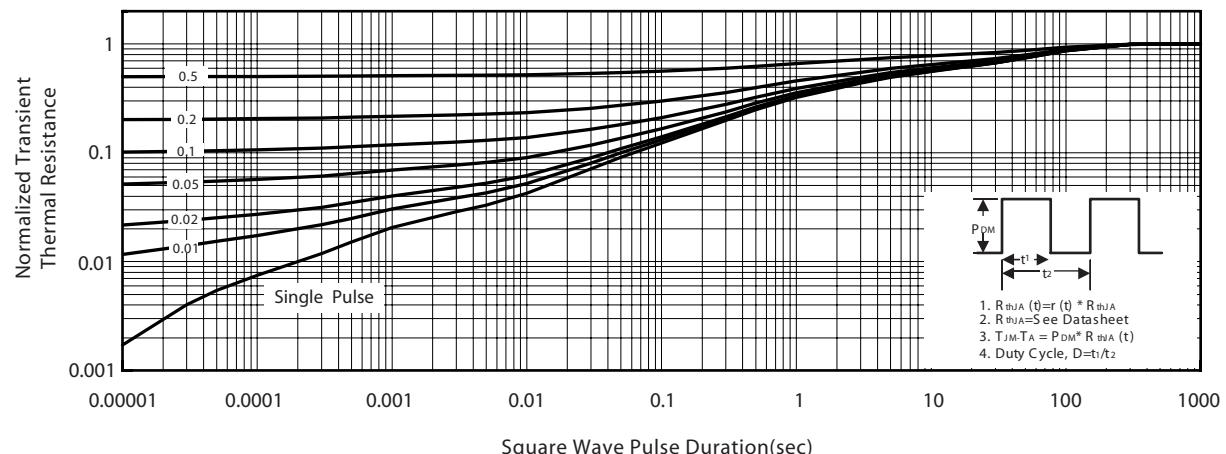
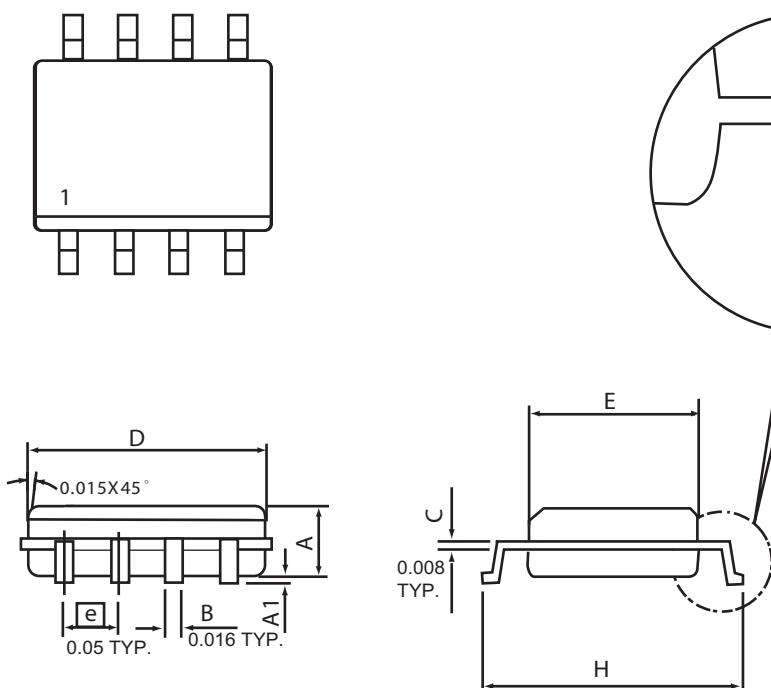


Figure 14. Normalized Thermal Transient Impedance Curve

## PACKAGE OUTLINE DIMENSIONS

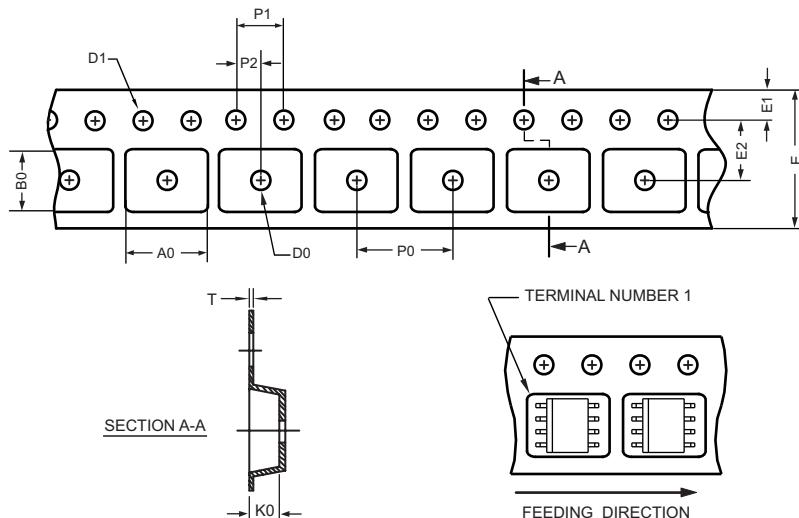
SO-8



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
D	4.80	4.98	0.189	0.196
E	3.81	3.99	0.150	0.157
H	5.79	6.20	0.228	0.244
L	0.41	1.27	0.016	0.050
θ	0°	8°	0°	8°

## SO-8 Tape and Reel Data

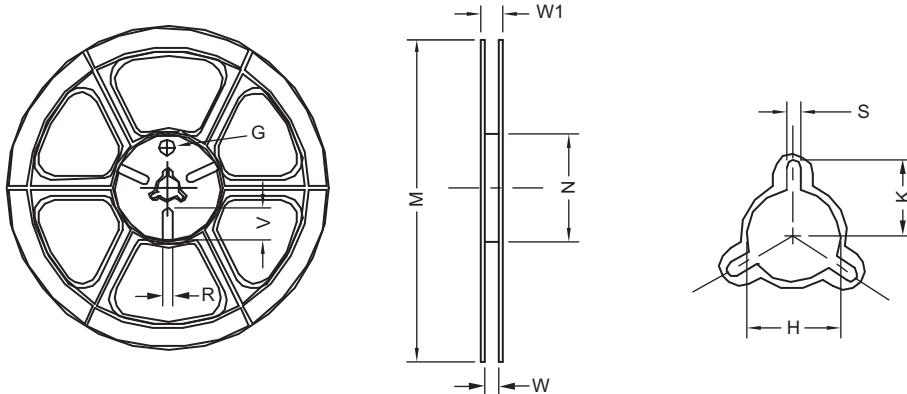
### SO-8 Carrier Tape



unit:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOP 8N 150mil	6.50 $\pm 0.15$	5.25 $\pm 0.10$	2.10 $\pm 0.10$	$\phi 1.5$ (MIN)	$\phi 1.55$ $\pm 0.10$	12.0 $+0.3$ $-0.1$	1.75 $\pm 0.10$	5.5 $\pm 0.10$	8.0 $\pm 0.10$	4.0 $\pm 0.10$	2.0 $\pm 0.10$	0.30 $\pm 0.013$

### SO-8 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	$\phi 330$	330 $\pm 1$	62 $\pm 1.5$	12.4 $+0.2$	16.8 $-0.4$	$\phi 12.75$ $+0.15$	---	2.0 $\pm 0.15$	---	---	---